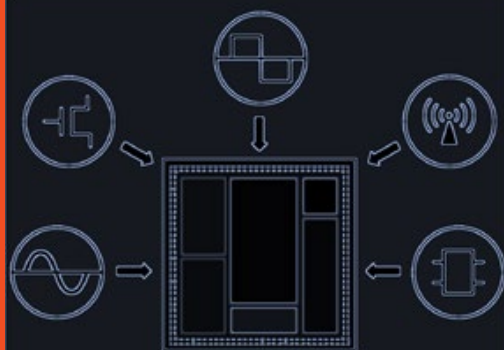




GLOBALFOUNDRIES®



130G/LP/EE

130 nm Process Technologies

Highlights

- 130G/LP Baseline Technology
 - + Manufactured in 300 mm facility in Singapore
 - + Volume production serving Mobile Cellular, Consumer and Digital/RF SoC
- 130EEPROM
 - + Extension of 130LP platform
 - + Leading EEPROM solution in the market
 - + Suitable for NFC, Smart Card, Consumer IC and MCU
- 110TS
 - + Cost optimized solution based on 130G platform
 - + For Bluetooth/RF SoC
- Comprehensive design ecosystem and services
 - + Full range of foundation and complex IP libraries
 - + eNVM IP including eFuse and OTP
- Extensive services and supply chain support
 - + Regularly scheduled MPWs
 - + Layout database consolidation and mask assembly services
 - + Industry-standard packaging and test solutions

Enabling *Connected Intelligence*

GLOBALFOUNDRIES 130 nm process technology platform is most suited for general purpose SoC designs and power- and price-sensitive applications.

The comprehensive, highly-configurable and production-proven 130 nm platform solution enables integration of logic, RF, analog and non-volatile memory to provide a cost effective solution. GF is also the first foundry to offer a 130 nm EEPROM solution. Further die cost reduction is made possible with the 110TS platform, which is shipping in volume production.

Analog + RF		Analog + RF		EEPROM
1.2 V	2.5 or 3.3 V	1.2 V	3.3 V	1.5 V
130G		110TS/G		130LP
130 nm process technology platform				

Target Applications and Solutions

- Bluetooth SoC (110TS)
- Cellular (GSM/EDGE, TD-SCDMA) Radio (130LP)
- WiFi Radio (130G, 130LP)
- Active RFID (130G, 130LP/EE)
- Mobile TV Tuner (130G, 130LP)
- Smart card / Bank card (130LP/EE)
- MEMS ASIC (130G, 130LP)
- Drones (130LP)

Technology Overview

- 130LP: 1.5 V (Core) and 3.3 V (I/O) solutions
 - + 2 core device Vt's
 - + Mixed-signal, high voltage, RF plug-in modules
- 130G: 1.2 V (Core) and 2.5/3.3 V (I/O) solutions
 - + 3 core device Vt's
 - + Mixed-signal, RF plug-in modules
- 110TS: 1.2 V (Core) and 3.3 V (I/O)
 - + Shrink from 130G
 - + Comparable performance to 130G
- EEPROM Module (130LP): High endurance, low power
- Twin retrograde wells on P-substrate
- MIM capacitor, eFuse fuse/macro
- High quality passives, diodes and inductors
- Standard temperature range: -40°C to 125°C

IP Overview

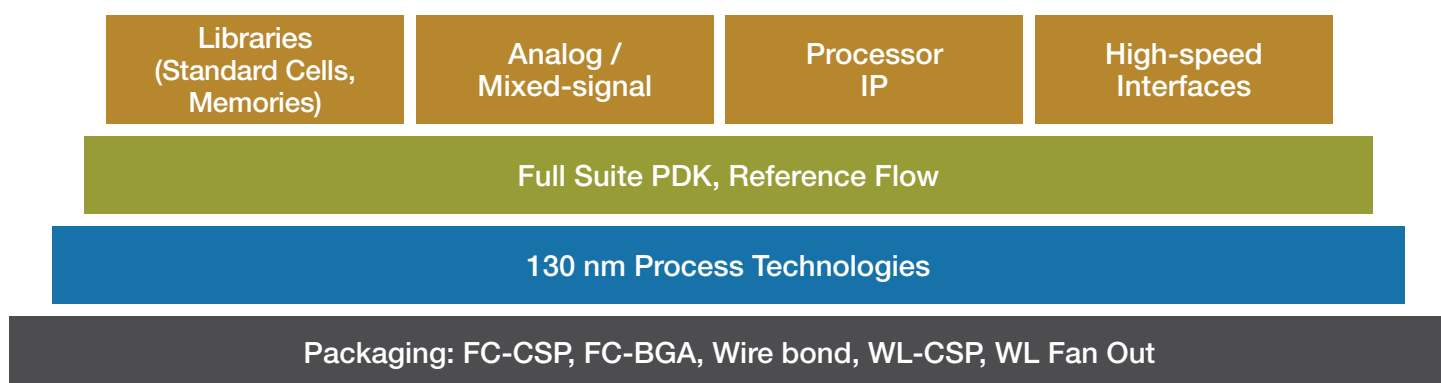
The comprehensive 130 nm Platform IP portfolio includes a wide range of silicon-proven high performance, power-optimized solutions for a broad set of applications.

Foundation IP		
Standard cell 1.5 V & 1.2 V (130LP)	Standard cell 1.2 V (130G)	GPIO
Memory		
High density memories	High speed memories (130LP)	
SRAM compiler	ROM Compiler	
Electrical Fuse macro	OTP macro	EEPROM
Analog IP		
DC-DC, PLL	Video DAC	Audio ADC/DAC
Interface IP		
SPIO (PCI)	USB 2.0 OTG/PHY	DDR DLL

Note: IP options vary by process selection.
Contact GF for IP availability.

GLOBALSOLUTIONS® Design and Manufacturing Ecosystem

GLOBALSOLUTIONS is the sum of our internal resources and ecosystem partners, combined to efficiently enable the fastest time-to-volume. This ecosystem includes partners in all aspects of design enablement and turnkey services, OPC and mask operations, and advanced capabilities in assembly solutions.



2600 Great America Way, Santa Clara, CA 95054 USA
Tel: +1 408-462-3900 globalfoundries.com/contact-us

The information contained herein is the property of GLOBALFOUNDRIES and/or its licensors. This document is for informational purposes only, is current only as of the date of publication and is subject to change by GLOBALFOUNDRIES at any time without notice. GLOBALFOUNDRIES, the GLOBALFOUNDRIES logo and combinations thereof are trademarks of GLOBALFOUNDRIES Inc. in the United States and/or other jurisdictions. Other product or service names are for identification purposes only and may be trademarks or service marks of their respective owners. © GLOBALFOUNDRIES Inc. 2018. Unless otherwise indicated, all rights reserved. Do not copy or redistribute except as expressly permitted by GLOBALFOUNDRIES.